第３回 関西コロキアム電子デバイスワークショップ
（第３回 MSFK Award 選考会）
IEEE EDS Kansai Chapter 総会

主催：　IEEE Electron Devices Society Kansai Chapter
共催：　京都大学、大阪大学
日時：　平成 15 年２月 25 日（火）午前 9 時 30 分～午後 3 時 30 分
会場：　キャンパスプラザ京都 第 1 会議室
場所：　〒600-8216 京都市下京区西洞院通塩小路下る
定員：　63 名
公用語：　日本語
会費：　2,000 円 （学生無料）
使用機器：　OHP、Projector 共に可
講演時間配分：一件に付き、発表 20 分、質疑応答５分
問い合わせ先：松下電器 酒井啓之（sakai@erl.mec.mei.co.jp）

Advance Program

9:30am Opening Remark by D. Ueda(Matsushita)

Technical Session A Chaired by T. Nakamura (Rohm)

9:40am A-1, “Novel Locally Strained Channel Technique for High Performance 55nm CMOS”, K. Ota, K. Sugihara, H. Sayama, T. Uchida, H. Oda, T. Eimori, H. Morimoto and Y. Inoue (Mitsubishi)

10:05am A-2, “A Study of Subband Structure and Transport of Two-Dimensional Holes in Strained Si p-MOSFETs Using Full-Band Modeling”, H. Nakatsuji, Y. Kamakura and K. Taniguchi (Osaka University)

10:30am A-3, “Novel Low Offset Voltage Diode using Asymmetric Threshold Voltage MONOS-FET for Next Generation Devices Demanding Low Voltage Operation”, S. Ueno, H. Furuta, Y. Okumura, T. Eimori and Y. Inoue, (Mitsubishi)

10:55am A-4, “A New Model of Time Evolution of Gate Leakage Current after Soft Breakdown in Ultra-Thin Gate Oxides”, T. Hosoi, P.L. Re, Y. Kamakura and K. Taniguchi (Osaka University)

11:15am A-5, Novel SOI Wafer Engineering Using Low Stress and High Mobility CMOSFET with <100>-Channel for Embedded RF/Analog Applications, T.

Matsumoto, S. Maeda, H. Dang, T. Uchida, K. Ota, Y. Hirano, H. Sayama, T. Iwamatsu, T. Ipposhi, H. Oda, S. Maegawa, Y. Inoue and T. Nishimura, (Mitsubishi)

11:40am～12:50pm Lunch Break

12:50pm Award Presentation by H. Nozawa(Kyoto University)

Technical Session B Chaired by M. Kuzuhara (NEC)

1:00pm B-1, "A High Efficiency InGaP/GaAs HBT Power Amplifier MMIC for the 5GHz Wireless-LAN Application", H. Koh, K. Sakuno, H. Kawamura, Y. Amano, M. Hasegawa, K. Kagoshima, K. Shirakawa, N. Takahashi, Y. Liu, T. Oka, K. Fujita, M. Yamashita, N. Matsumoto and H. Sato (Sharp)

1:25pm B-2, "Improved RF Characteristics of InGaP/GaAs HBT by using Novel Ledge Coupled Capacitor(LCC) Structure", N. Tsurumi, M. Yanagihara, M. Ishii, M. Nishijima, T. Tanaka and D. Ueda (Matsushita)

1:50pm B-3, "2.3W AlGaN/GaN Power Heterojunction FET at Ka-band", T.Inoue, K. Kasahara, H.Miyamoto, Y.Ando, Y.Okamoto, T.Nakayama, and M.Kuzuhara (NEC)

2:15pm B-4, "Low Noise Performance of AlGaN/GaN HFETs and its relevance to the epi-layer defect density" Y. Hirose, Y. Ikeda, M.Ishii, T. Murata, K.Inoue and T. Tanaka, H. Ishikawa*, T. Egawa* and T. Jimbo*, (Matsushita, *Nagoya Institute of Technology)

2:40pm B-5, "Avalanche Phenomena in 4H-SiC p-n Diodes Fabricated by Aluminum or Boron Implantation", Y. Negoro, N. Miyamoto, T. Kimoto and H. Matsunami, (Kyoto University)

3:05pm Closed Remark by K. Taniguchi (Osaka University)

3:15pm～ IEEE EDS Kansai Chapter 総会

議題

1. 2003～2004 年度新役員の件
2. 国際会議 The 2003 International Meeting for Future Electron Devices, Kansai の件

3. その他